

PTO/SB/05b (02-09)

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Substitute for form 1449/PTO				Complete if Known	
				Application Number	10/581,950-Conf. #8737
				Filing Date	August 18, 2008
				First Named Inventor	Anderson
				Art Unit	2822 2894
				Examiner Name	D. T. Nguyen
Sheet	1	of	1	Attorney Docket Number	GWS-008

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
A12*	US-5,945,730	08-31-1999	Sicard et al.		
A13*	US-6,261,944	07-17-2001	Meha et al.		
A14*	US-6,507,070	01-14-2003	Shen et al.		
A15*	US-6,586,323	07-01-2003	Fan et al.		
A16*	US-6,674,157	01-06-2004	Lang		
A17*	US-6,861,702	03-01-2005	Kitamura et al.		
A18*	US-6,936,923	08-30-2005	Lin et al.		
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FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
B1	WO-2005-057617 A3		06-23-2005	Great Wall Semiconductor	T ⁶

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue numbers, publisher, city and/or country where published.			
C4	Darwish et al., "Scaling Issues in Lateral Power MOSFETs," Proc. 1998 Intl. Symp. On Power Semiconductor Devices & Ics, pp. 329-332.				
C5	International Search Report and Written Opinion for PCT/US2004/040698, dated August 8, 2005.				
C6	International Search Report and Written Opinion for PCT/US2004/40197, mailed November 21, 2008.				
C7	Pavier et al., "Bi-directional FlipFET™ MOSFETs for Cell Phone Battery Protection Circuits," PCIM 2001.				
C8	Shen et al., "Lateral Discrete Power MOSFET: Enabling Technology for Next-Generation, MHz-Frequency, High-Density DC/DC Converters," APEC (2004).				
C9	Sun et al., ""0.35µm, 43 µΩcm ² 6mΩ Power MOSFET to Power Future Microprocessor," IEEE pp. 77-79 (1999).				
Examiner Signature	/Duy Nguyen/	Date Considered	06/02/2009		

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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